## 2SC5295J

## Silicon NPN epitaxial planar type

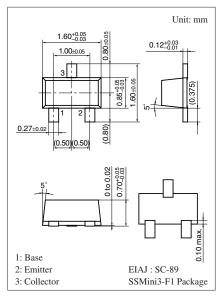
#### For 2 GHz band low-noise amplification

#### ■ Features

- High transition frequency f<sub>T</sub>
- Low collector output capacitance Cob
- SS-mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	15	V
Collector to emitter voltage	$V_{CEO}$	10	V
Emitter to base voltage	$V_{EBO}$	2	V
Collector current	$I_C$	65	mA
Collector power dissipation	$P_{C}$	125	mW
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C



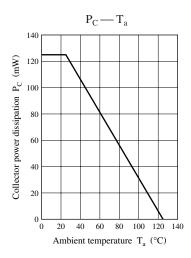
Marking Symbol: 3S

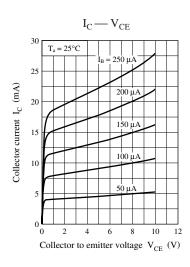
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

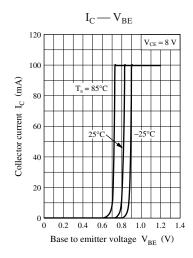
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_E = 0$			1	μΑ
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 1 \text{ V}, I_{C} = 0$			1	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}$	50		170	
Gain bandwidth product	$f_T$	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 1.5 \text{ GHz}$	7.0	8.5		GHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.6	1.0	pF
Forward transfer gain	S <sub>21e</sub>   2	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 1.5 \text{ GHz}$	7	9		dB
Maximum unilateral power gain	GUM	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 1.5 \text{ GHz}$		10		dB
Noise figure	NF	$V_{CE} = 8 \text{ V}, I_{C} = 7 \text{ mA}, f = 1.5 \text{ GHz}$		2.2	3.0	dB

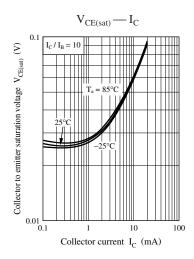
Note)  $*: h_{FE}$  rank classification

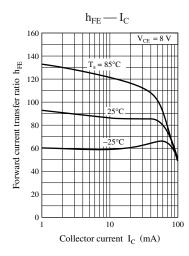
Rank	Q	R
$h_{FE}$	50 to 120	100 to 170

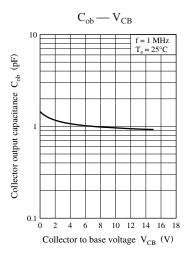












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